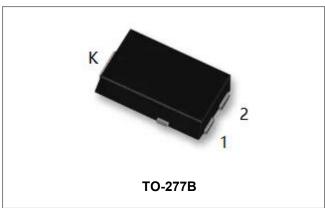
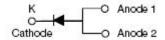




# ST2080S SCHOTTKY RECTIFIER



**Circuit Diagram** 



#### **Features**

- 150°C T<sub>J</sub> operation
- Center tap configuration
- Low forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- High frequency operation
- Trench MOS Schottky technology
- Terminals finish: 100% Pure Tin
- "-A" is an AEC-Q101 qualified device
- This is a Halogen Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

#### **Applications**

- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection

### Maximum Ratings(limiting values, at 25 °C unless otherwise specified)

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V <sub>RRM</sub> V <sub>RWM</sub> V <sub>R</sub>	-	80	V
Average Rectified Forward Current	I <sub>F (AV)</sub>	T <sub>C</sub> =112°C, In DC	20	Α
Peak One Cycle Non-Repetitive Surge Current	I <sub>FSM</sub>	8.3ms, Half Sine pulse	150	А

#### **Electrical Characteristics:**

Characteristics	Symbol	Condition	Тур.	Max.	Units
Forward Voltage Drop*	$V_{F1}$	@ 10A, Pulse, T <sub>J</sub> = 25 °C @ 20A, Pulse, T <sub>J</sub> = 25 °C	0.51 0.62	- 0.70	٧
	$V_{F2}$	@ 10A, Pulse, T <sub>J</sub> = 125 °C @ 20A, Pulse, T <sub>J</sub> = 125 °C	0.45 0.57	- 0.65	V
Reverse Current*	I <sub>R1</sub>	@V <sub>R</sub> = rated V <sub>R,</sub> T <sub>J</sub> = 25 °C	24	300	uA
	$I_{R2}$	$@V_R = \text{rated } V_{R_1} T_J = 125  ^{\circ}\text{C}$	16	75	mA
Junction Capacitance	Ст	$@V_R = 5V, T_C = 25 °C f_{SIG} = 1MHz$	1041	-	pF

<sup>\*</sup> Pulse width < 300 µs, duty cycle < 2%

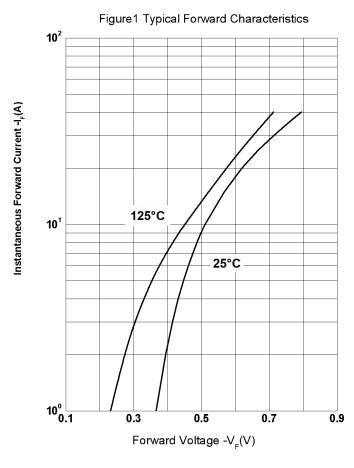


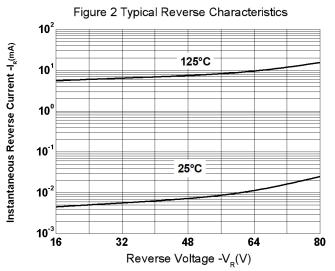


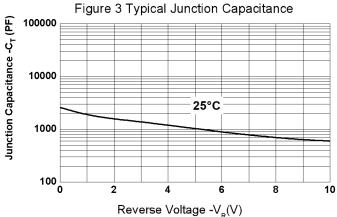
# **Thermal-Mechanical Specifications:**

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	TJ	-	-55 to +150	°C
Storage Temperature	T <sub>stg</sub>	-	-55 to +150	°C
Typical Thermal Resistance Junction to Case	R <sub>θ</sub> JC	-	3.5	°C/W
Typical Thermal Resistance Junction to Ambient	R <sub>θJA</sub>		70	°C/W
Approximate Weight	wt	-	0.08	g

# **Ratings and Characteristics Curves**







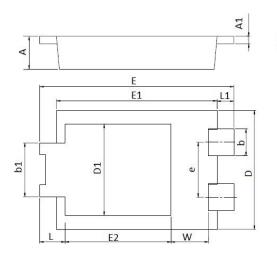
<sup>•</sup> China - Germany - Korea - Singapore - United States •

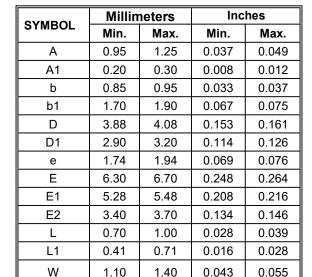
<sup>•</sup> http://www.smc-diodes.com - sales@ smc-diodes.com •



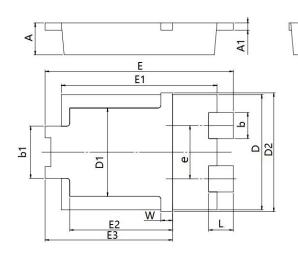


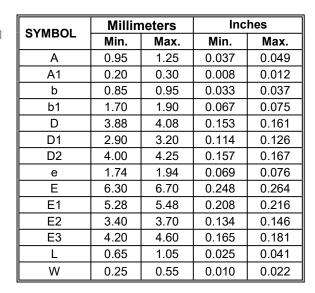
#### **Mechanical Dimensions TO-277B**





#### **Mechanical Dimensions TO-277B(New)**





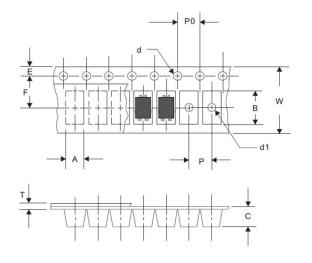
Notes: New Mechanical Dimensions is performed from date code 2236X.

<sup>•</sup> http://www.smc-diodes.com - sales@ smc-diodes.com •





# **Carrier Tape Specification TO-277B**



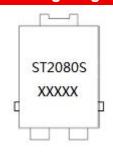
SYMBOL	Millimeters		
STIVIBUL	Min.	Max.	
Α	4.28	4.48	
В	6.80	7.10	
С	1.30	1.50	
d	1.40	1.60	
d1	-	1.50	
E	1.65	1.85	
F	5.40	5.60	
Р	7.90	8.10	
P0	3.90	4.10	
Т	0.24	0.44	
W	11.70	12.30	

# **Ordering Information**

Device	Package	Shipping
ST2080S	TO-277B(Pb-Free)	5000pcs/ reel
ST2080STR	TO-277B(Pb-Free)	5000pcs/ reel

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

# **Marking Diagram**



Where XXXXX is YYWWL

 ST
 = Device Type

 20
 = Forward Current (20A)

 80
 = Reverse Voltage (80V)

 S
 = Package type

 YY
 = Year

 WW
 = Week

 L
 = Lot Number

Cautions: Molding resin

Epoxy resin UL:94V-0





#### DISCLAIMER:

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- 2- In cases where extremely high reliability is required (such as use in nuclear power control, aerospace and aviation, traffic equipment, medical equipment, and safety equipment), safety should be ensured by using semiconductor devices that feature assured safety or by means of users' fail-safe precautions or other arrangement.
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